

TVS Diodes

Transient Voltage Suppressor Diodes

ESD3V3U1U Series

Uni-directional Ultra-low Capacitance ESD / Transient Protection Diode

ESD3V3U1U-02LS
ESD3V3U1U-02LRH

Data Sheet

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Revision History

| Page or Item | Subjects (major changes since previous revision) |
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| Revision 1.0, 2011-04-12 | |
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Table of Contents

| | | |
|----------|---|----|
| | Table of Contents | 4 |
| | List of Figures | 5 |
| | List of Tables | 6 |
| 1 | Uni-directional Ultra-low Capacitance ESD / Transient Protection Diode | 7 |
| 1.1 | Features | 7 |
| 1.2 | Application Examples | 7 |
| 2 | Product Description | 7 |
| 3 | Characteristics | 8 |
| 3.1 | Electrical Characteristics at $T_A = 25\text{ °C}$, unless otherwise specified | 8 |
| 3.2 | Typical Characteristics at $T_A=25\text{°C}$, unless otherwise specified | 10 |
| 4 | Application Information | 13 |
| 5 | Ordering Information Scheme (Examples) | 14 |
| 6 | Package Information | 15 |
| 6.1 | PG-TSSLP-2-1 (mm) [3] | 15 |
| 6.2 | PG-TSLP-2-7 (mm)[3] | 16 |
| | Terminology | 17 |
| | References | 18 |

List of Figures

| | | |
|-----------|---|----|
| Figure 1 | Pin Configuration and Schematic Diagram | 7 |
| Figure 2 | Definitions of Electrical Characteristics | 8 |
| Figure 3 | Line capacitance $C_L=f(V_R)$ $f = 1\text{MHz}$, from pin 1 to pin 2 | 10 |
| Figure 4 | Line capacitance $C_L=f(f)$, from pin 1 to pin 2 | 10 |
| Figure 5 | Line capacitance $C_L=f(T_A)$, from pin 1 to pin 2 | 11 |
| Figure 6 | Reverse current $I_R=f(T_A)$, $V_R=3.3\text{ V}$, from pin 1 to pin 2 | 11 |
| Figure 7 | Clamping voltage $V_{TLP}=f(I_{TLP})$, from pin 1 to pin 2[1] | 12 |
| Figure 8 | Forward clamping voltage $V_{TLP}=f(I_{TLP})$, from pin 2 to pin 1[1] | 12 |
| Figure 9 | Single line, uni-directional ESD / Transient protection[2] | 13 |
| Figure 10 | Ordering information scheme | 14 |
| Figure 11 | PG-TSSLP-2-1: Package overview | 15 |
| Figure 12 | PG-TSSLP-2-1: Footprint | 15 |
| Figure 13 | PG-TSSLP-2-1: Packing | 15 |
| Figure 14 | PG-TSSLP-2-1: Marking (example) | 15 |
| Figure 15 | PG-TSLP-2-7: Package overview | 16 |
| Figure 16 | PG-TSLP-2-7: Footprint | 16 |
| Figure 17 | PG-TSLP-2-7: Packing | 16 |
| Figure 18 | PG-TSLP-2-7: Marking (example) | 16 |

List of Tables

| | | |
|---------|--|---|
| Table 1 | Ordering Information | 7 |
| Table 2 | Maximum Rating at $T_A = 25\text{ °C}$, unless otherwise specified | 8 |
| Table 3 | DC Characteristics at $T_A = 25\text{ °C}$, unless otherwise specified | 8 |
| Table 4 | RF Characteristics at $T_A = 25\text{ °C}$, unless otherwise specified | 9 |
| Table 5 | ESD Characteristics at $T_A = 25\text{ °C}$, unless otherwise specified | 9 |

1 Uni-directional Ultra-low Capacitance ESD / Transient Protection Diode

1.1 Features

- ESD / Transient protection of high speed data lines exceeding
 - IEC61000-4-2 (ESD): ± 20 kV (air / contact)
 - IEC61000-4-4 (EFT): 2.5 kV / 50 A (5/50 ns)
 - IEC61000-4-5 (surge): 3 A (8/20 μ s)
- Maximum working voltage: $V_{RWM} = 3.3$ V
- Ultra low capacitance: $C_L = 0.4$ pF (typical)
- Low clamping voltage, low dynamic resistance $R_{DYN} = 0.6 \Omega$ (typical)
- Pb-free (RoHS compliant) and halogen free package, very small form factor down to $0.62 \times 0.32 \times 0.31$ mm³



1.2 Application Examples

- HDMI, USB 2.0/USB 3.0, DisplayPort, DVI
- 10/100/1000 Ethernet, Firewire, S-ATA
- Mobile HDMI Link, MDDI, MIPI, etc.

2 Product Description

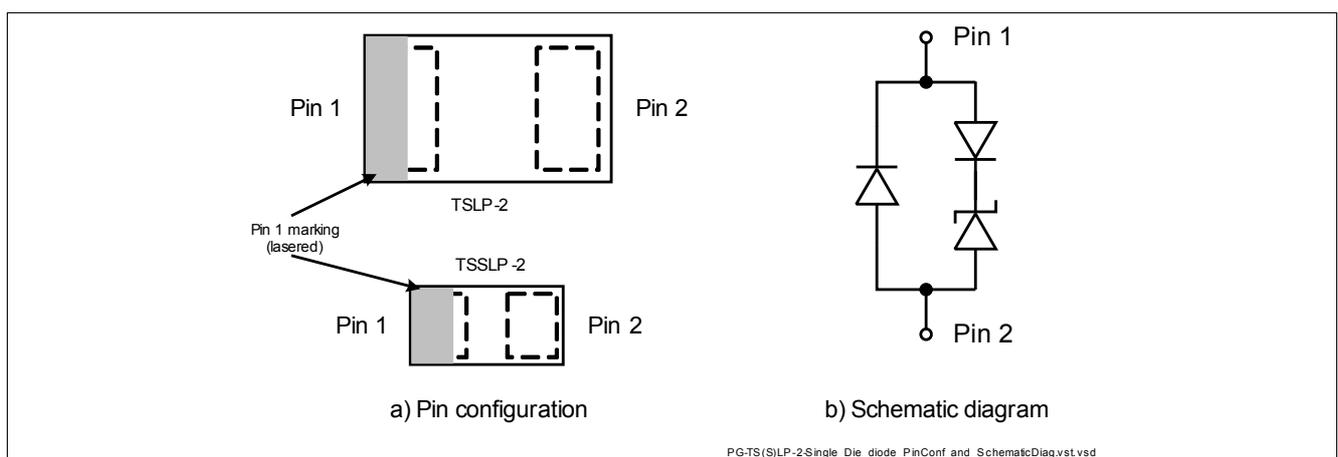


Figure 1 Pin Configuration and Schematic Diagram

Table 1 Ordering Information

| Type | Package | Configuration | Marking code |
|-----------------|--------------|-------------------------|--------------|
| ESD3V3U1U-02LS | PG-TSSLP-2-1 | 1 line, uni-directional | Z |
| ESD3V3U1U-02LRH | PG-TSLP-2-7 | 1 line, uni-directional | E3 |

3 Characteristics

Table 2 Maximum Rating at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|--|-----------|--------|------|------|------------------|
| | | Min. | Typ. | Max. | |
| ESD (air / contact) discharge ¹⁾ | V_{ESD} | – | – | 20 | kV |
| Peak pulse current ($t_p = 8/20\text{ }\mu\text{s}$) ²⁾ | I_{PP} | – | – | 3 | A |
| Operating temperature range | T_{OP} | -55 | – | 125 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -65 | – | 150 | $^\circ\text{C}$ |

1) V_{ESD} according to IEC61000-4-2

2) I_{PP} according to IEC61000-4-5

3.1 Electrical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

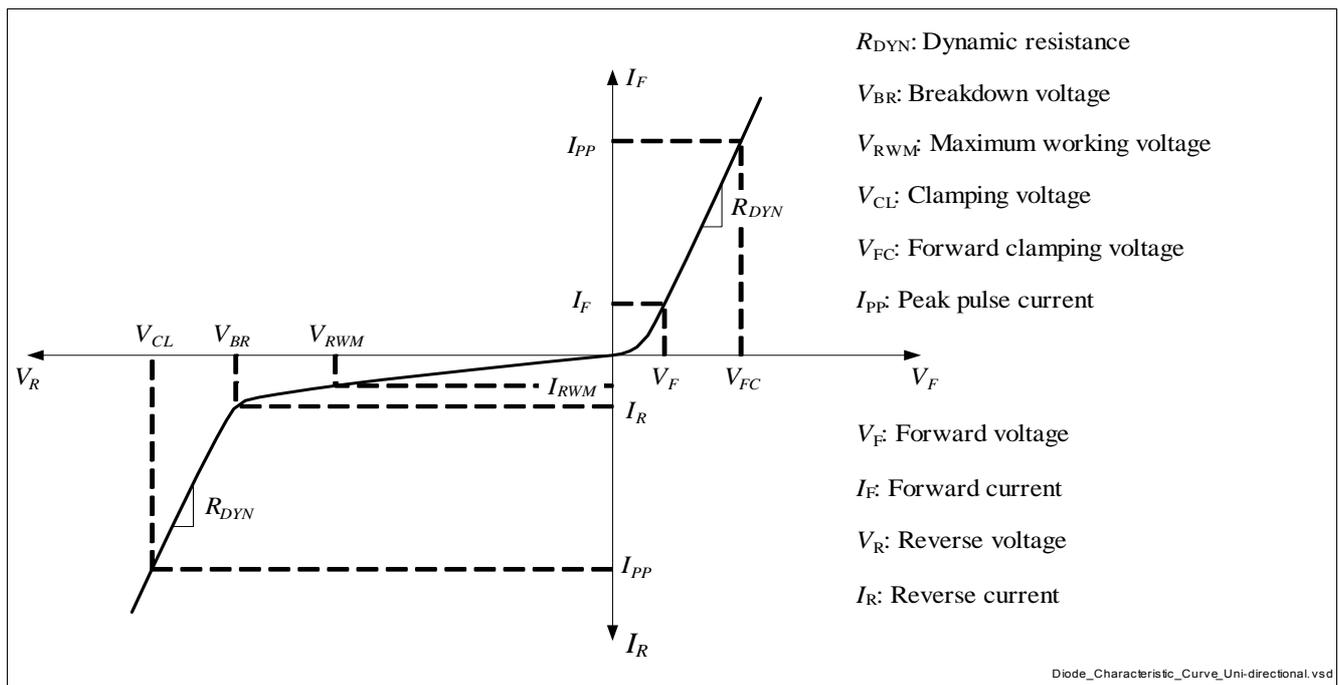


Figure 2 Definitions of Electrical Characteristics

Table 3 DC Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|-------------------------|-----------|--------|------|------|------|--|
| | | Min. | Typ. | Max. | | |
| Reverse working voltage | V_{RWM} | – | – | 3.3 | V | Pin 1 to Pin 2 |
| Breakdown voltage | V_{BR} | 5 | – | – | V | $I_{BR} = 1\text{ mA}$, from Pin 1 to Pin 2 |
| Reverse current | I_R | – | <1 | 50 | nA | $V_R = 3.3\text{ V}$, from Pin 1 to Pin 2 |

Table 4 RF Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--------------------------------|--------|--------|------|------|------|--------------------------------------|
| | | Min. | Typ. | Max. | | |
| Line capacitance ¹⁾ | C_L | – | 0.4 | 0.6 | pF | $V_R = 0\text{ V}, f = 1\text{ MHz}$ |
| Serie inductance | L_S | – | 0.2 | – | nH | ESD3V3U1U-02LS |
| | | – | 0.4 | – | nH | ESD3V3U1U-02LRH |

1) Total capacitance line to ground

Table 5 ESD Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|----------------------------------|-----------|--------|------|------|----------|---|
| | | Min. | Typ. | Max. | | |
| Clamping voltage | V_{CL} | – | 19 | – | V | $I_{PP} = 16\text{ A}$, from Pin 1 to Pin 2 |
| | | – | 28 | – | V | $I_{PP} = 30\text{ A}$, from Pin 1 to Pin 2 |
| Forward clamping voltage | V_{FC} | – | 10 | – | V | $I_{PP} = 16\text{ A}$, from Pin 2 to Pin 1 |
| | | – | 17 | – | V | $I_{PP} = 30\text{ A}$, from Pin 2 to Pin 1 |
| Dynamic resistance ¹⁾ | R_{DYN} | – | 0.6 | – | Ω | Pin 1 to Pin 2 |
| | | – | 0.5 | – | Ω | Pin 2 to Pin 1 |

1) Please refer to Application Note AN210. TLP parameter: $Z_0 = 50\ \Omega$, $t_p = 100\text{ ns}$, $t_r = 300\text{ ps}$, averaging window: $t_1 = 30\text{ ns}$ to $t_2 = 60\text{ ns}$, extraction of dynamic resistance using least squares fit of TLP characteristics between $I_{PP1} = 10\text{ A}$ and $I_{PP2} = 40\text{ A}$.

3.2 Typical Characteristics at $T_A=25^\circ\text{C}$, unless otherwise specified

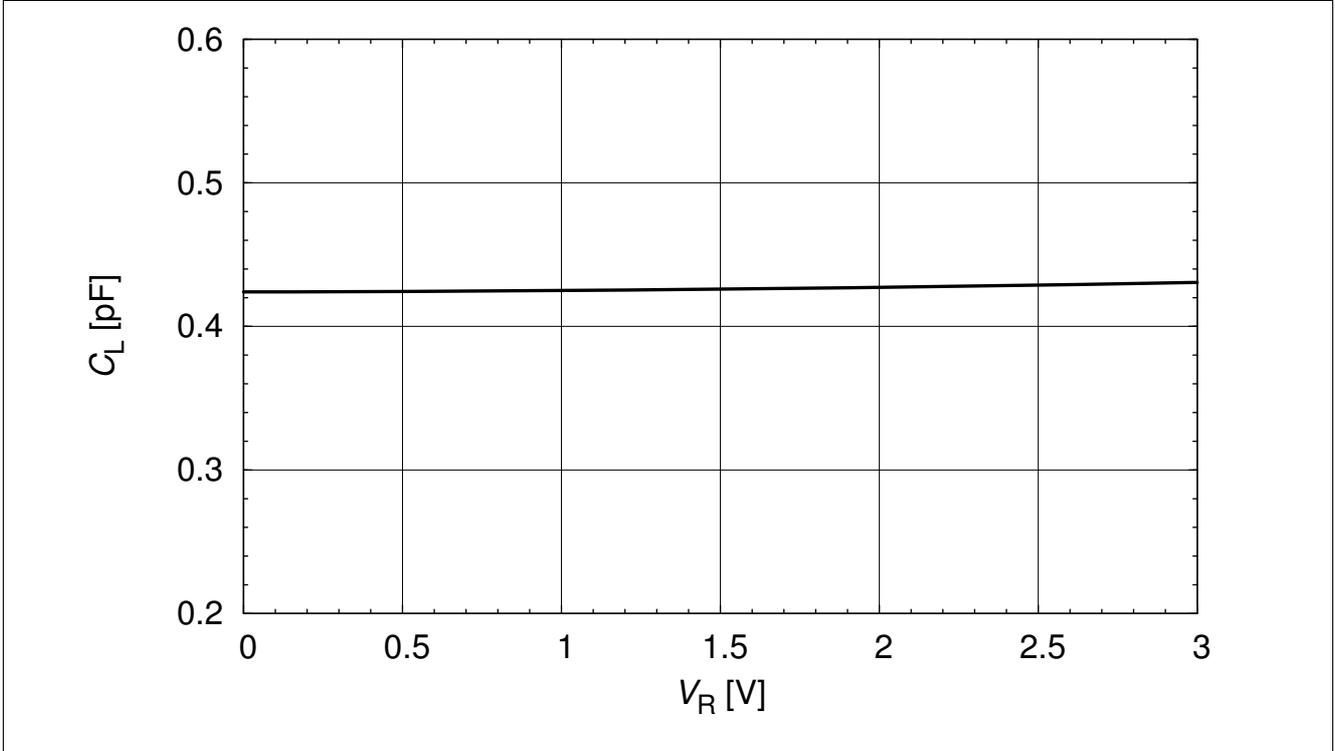


Figure 3 Line capacitance $C_L=f(V_R)$ $f = 1\text{MHz}$, from pin 1 to pin 2

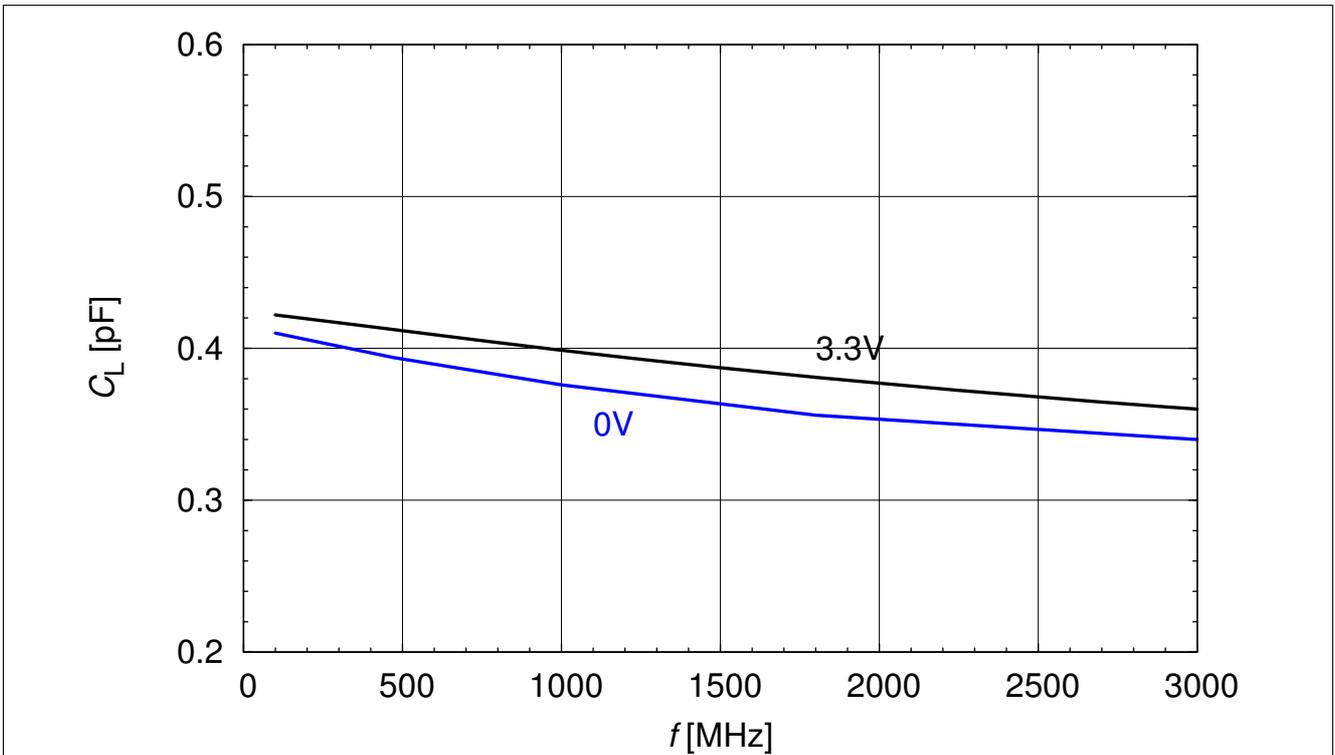


Figure 4 Line capacitance $C_L=f(f)$, from pin 1 to pin 2

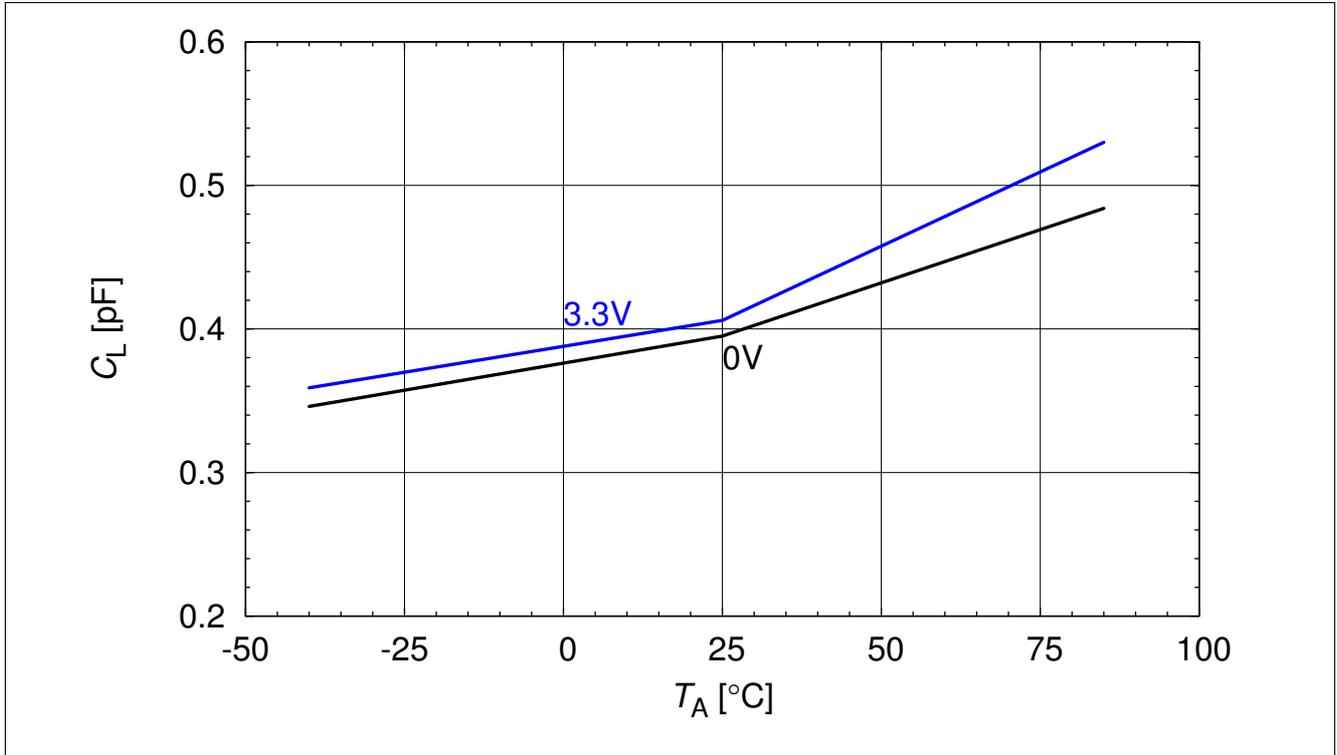


Figure 5 Line capacitance $C_L=f(T_A)$, from pin 1 to pin 2

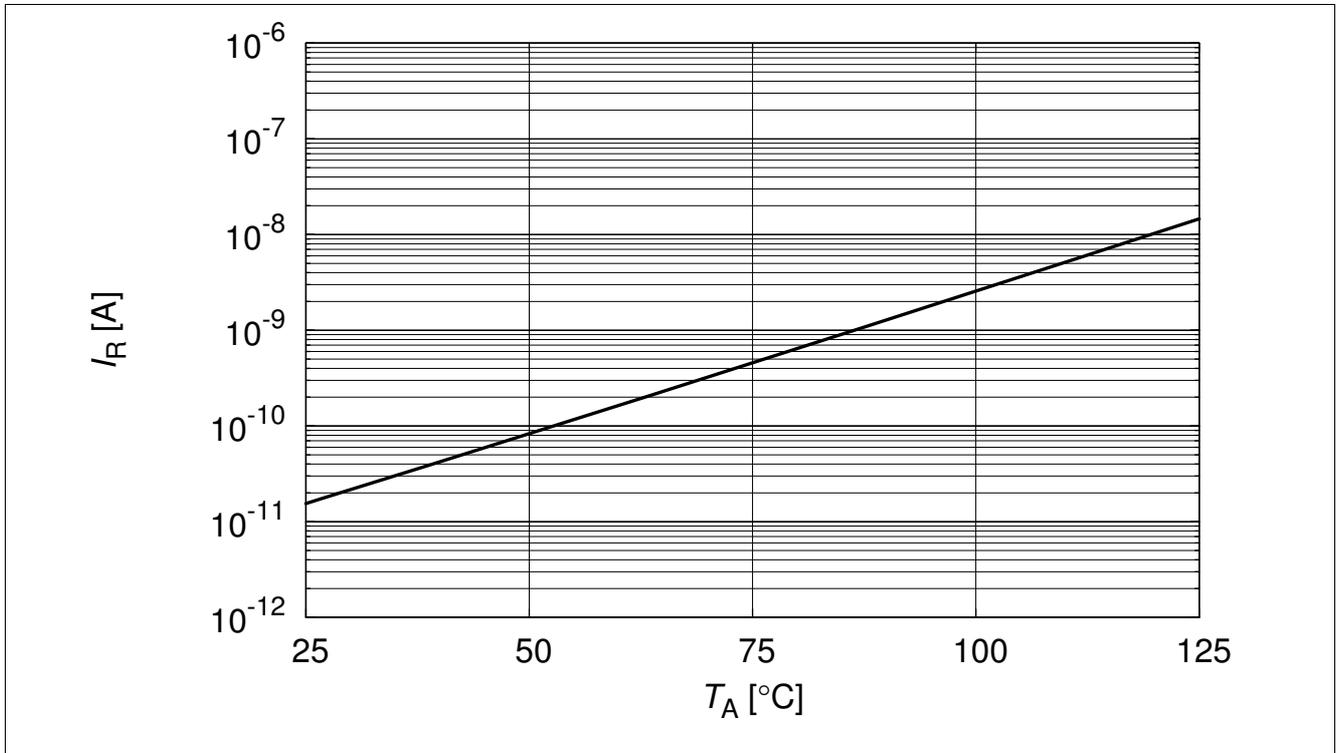


Figure 6 Reverse current $I_R=f(T_A)$, $V_R=3.3 V$, from pin 1 to pin 2

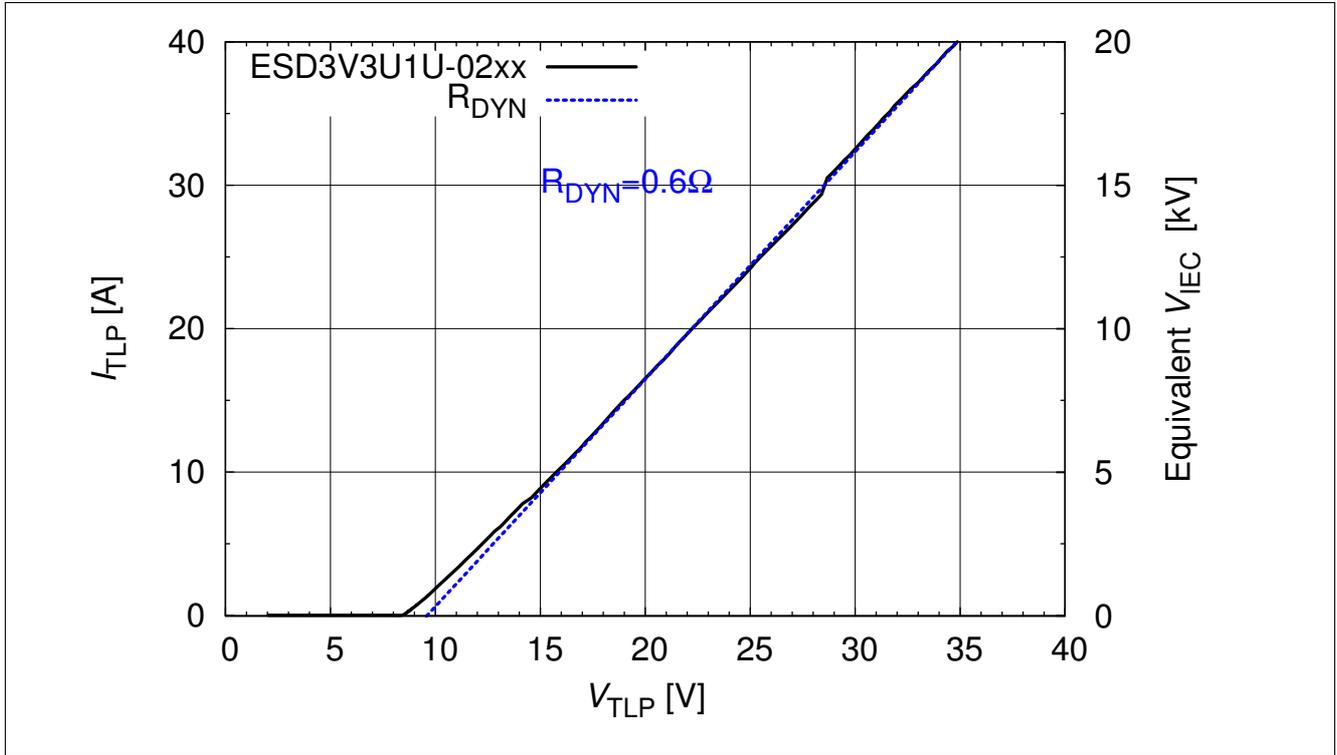


Figure 7 Clamping voltage $V_{TLP}=f(I_{TLP})$, from pin 1 to pin 2[1]

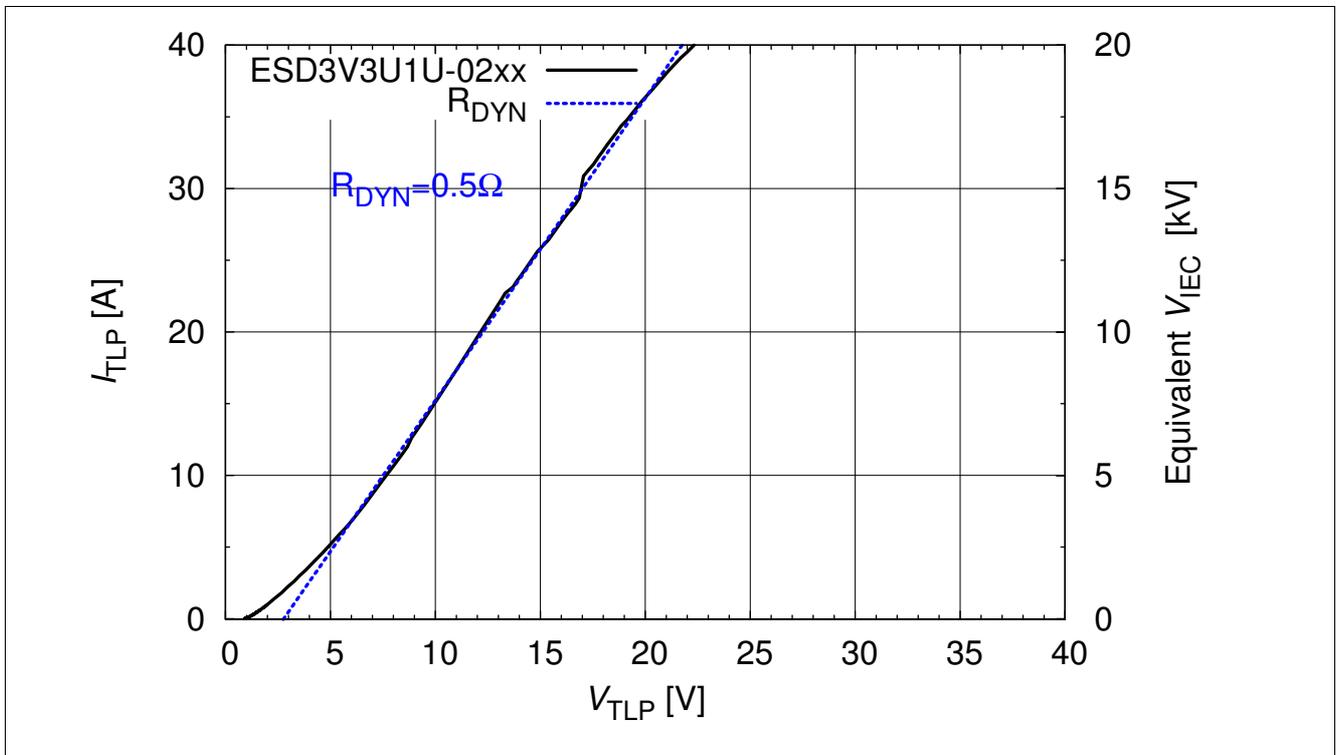


Figure 8 Forward clamping voltage $V_{TLP}=f(I_{TLP})$, from pin 2 to pin 1[1]

4 Application Information

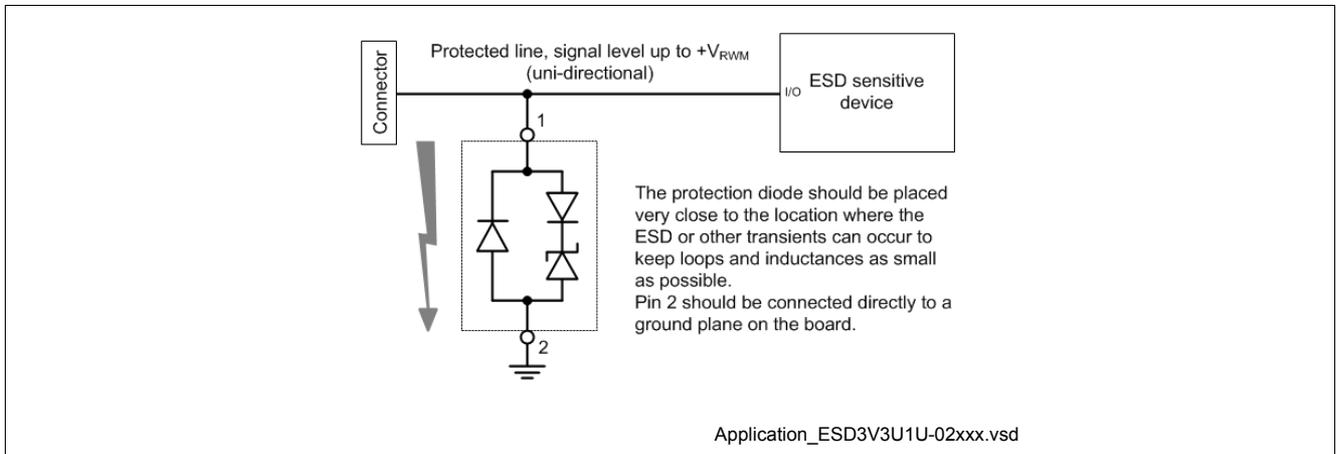


Figure 9 Single line, uni-directional ESD / Transient protection[2]

5 Ordering Information Scheme (Examples)

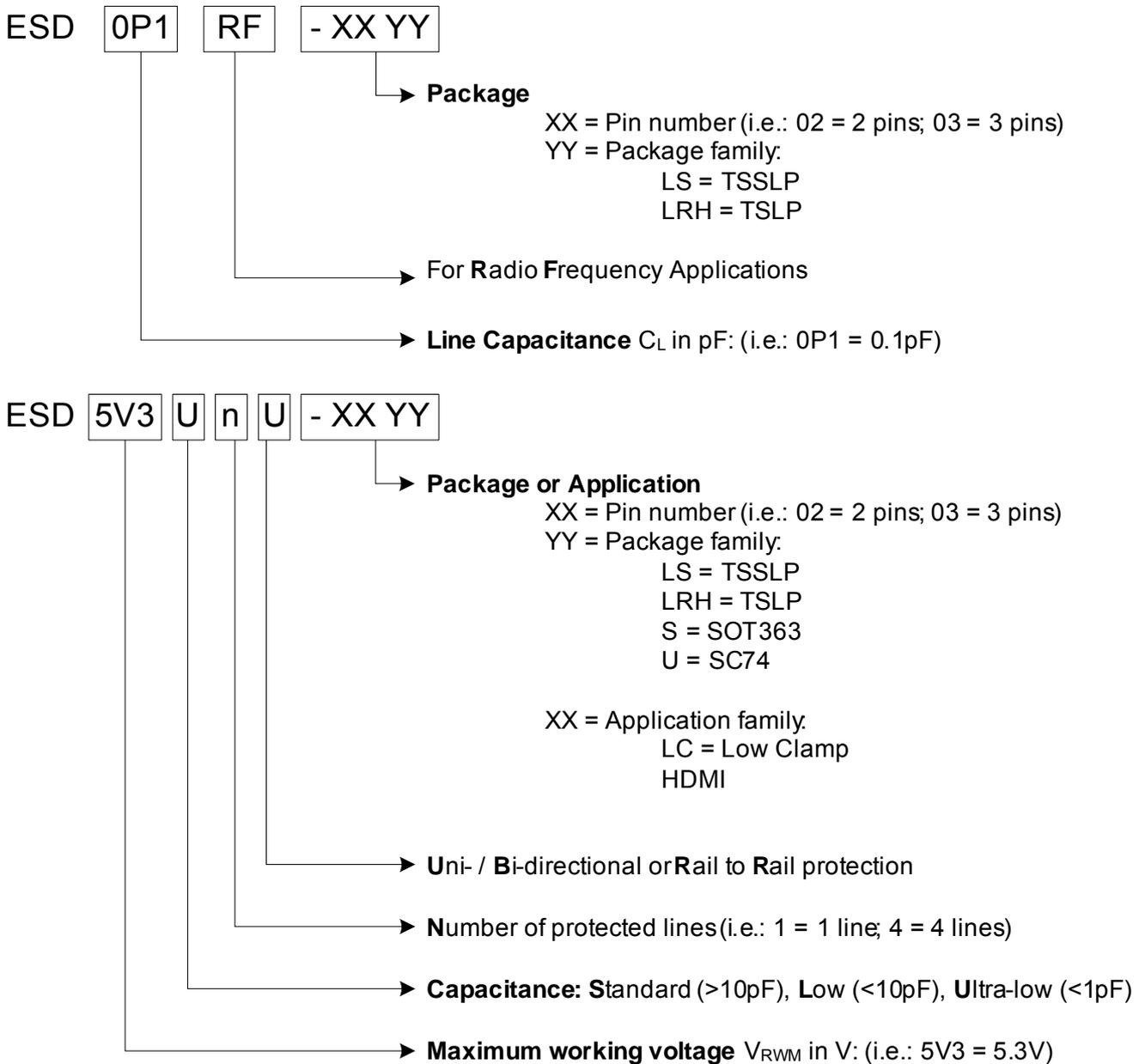


Figure 10 Ordering information scheme

6 Package Information

6.1 PG-TSSLP-2-1 (mm) [3]

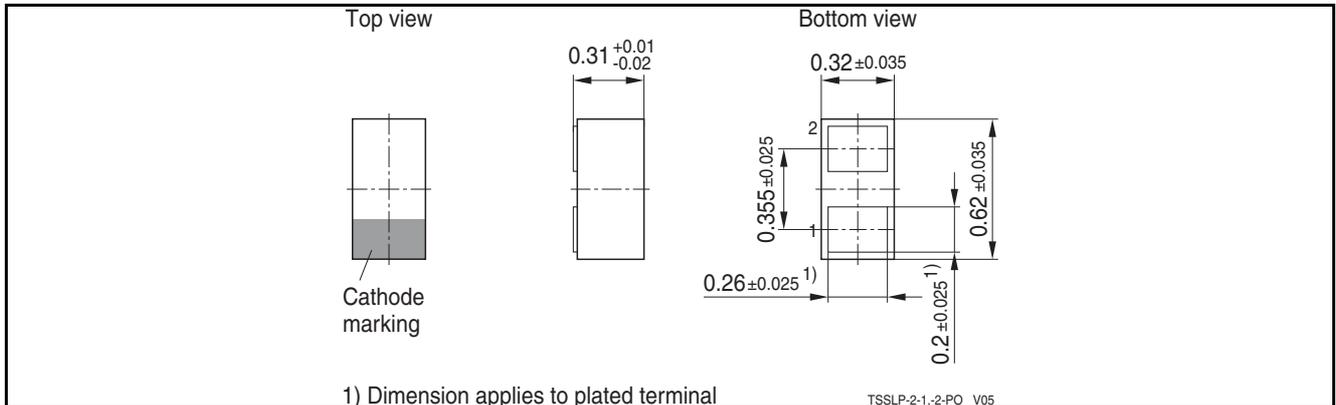


Figure 11 PG-TSSLP-2-1: Package overview

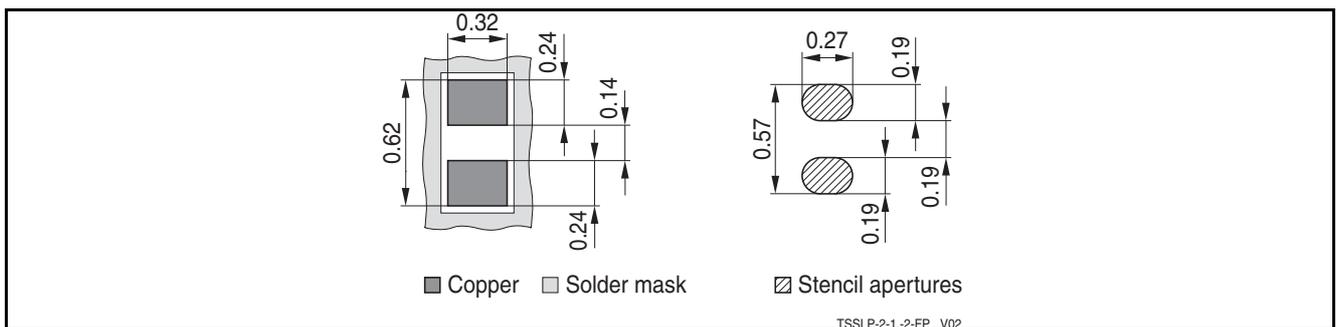


Figure 12 PG-TSSLP-2-1: Footprint

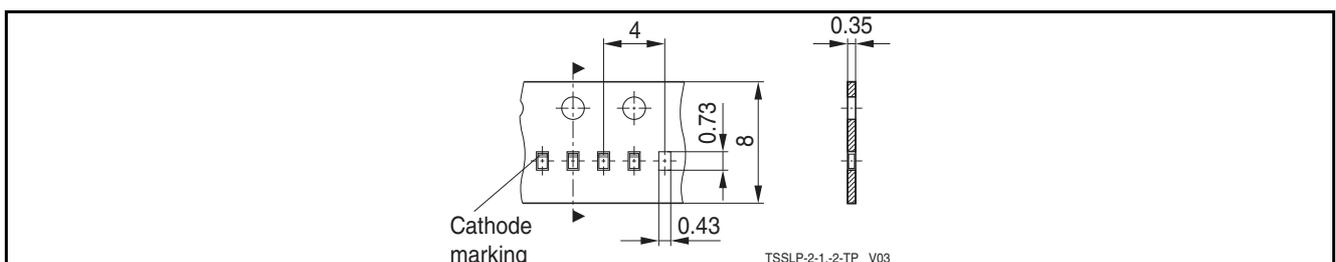


Figure 13 PG-TSSLP-2-1: Packing

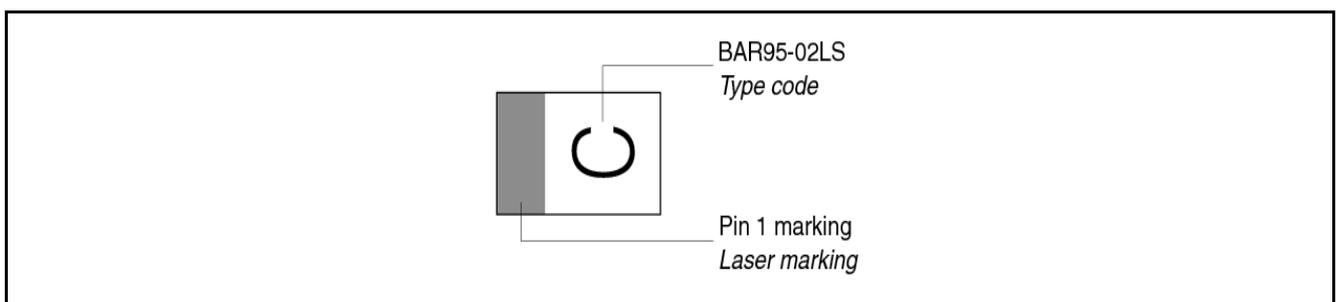


Figure 14 PG-TSSLP-2-1: Marking (example)

6.2 PG-TSLP-2-7 (mm)[3]

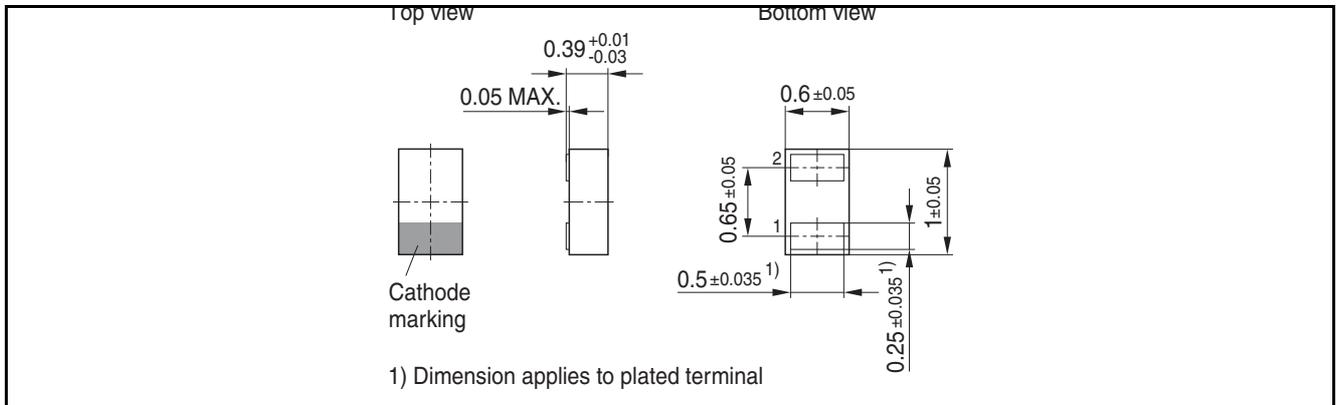


Figure 15 PG-TSLP-2-7: Package overview

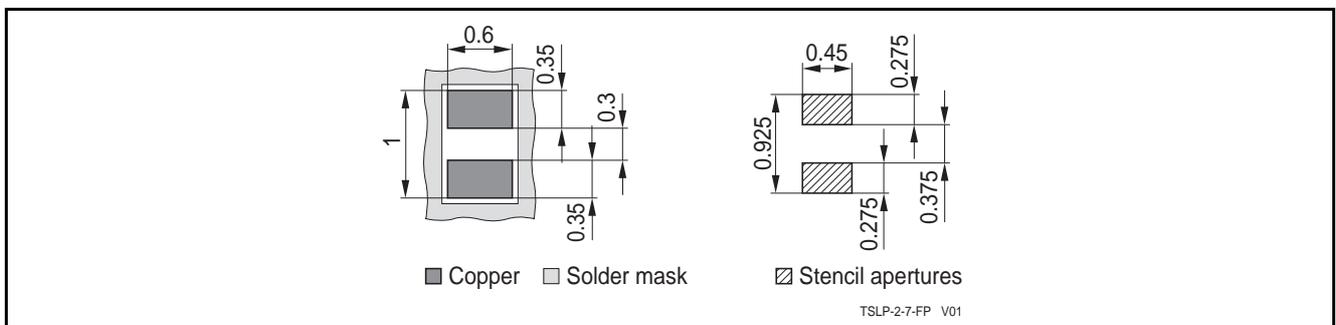


Figure 16 PG-TSLP-2-7: Footprint

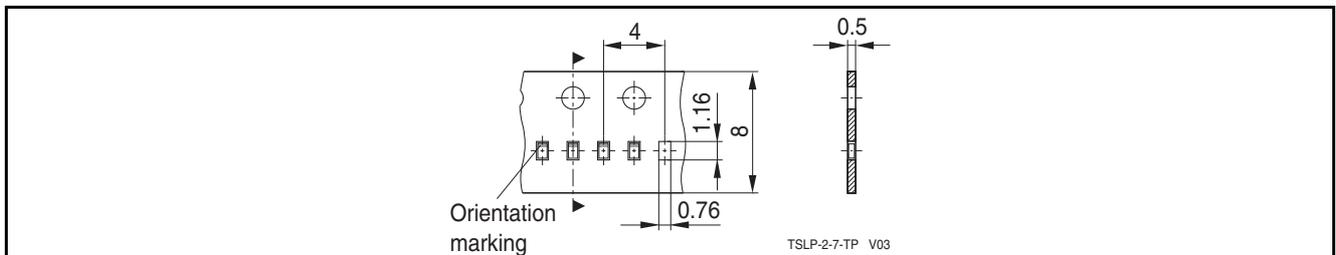


Figure 17 PG-TSLP-2-7: Packing

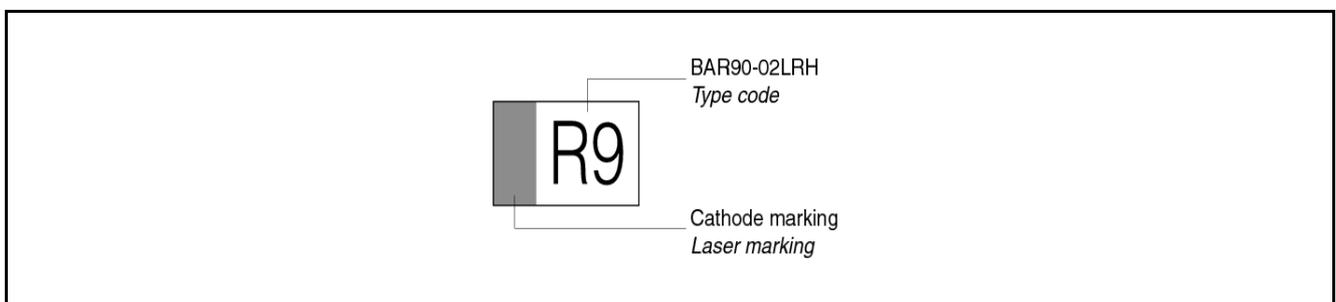


Figure 18 PG-TSLP-2-7: Marking (example)

Terminology

| | |
|-------------|---|
| C_L | Line capacitance |
| EFT | Electrical Fast Transient |
| ESD | Electrostatic Discharge |
| HDMI | High Definition Multimedia Interface |
| IEC | International Electrotechnical Commission |
| I_{PP} | Peak pulse current |
| I_R | Reverse current |
| I_{RWM} | Maximum Reverse working Current |
| LCD | Liquid Crystal Display |
| L_S | Serial inductance |
| MDDI | Mobile Display Digital Interface |
| MIPI | Mobile Industrial Processor Interface |
| RoHS | Restriction of Hazardous Substances Directive |
| S-ATA | Serial Advanced Technology Attachment |
| T_A | Ambient temperature |
| T_{OP} | Operation temperature |
| t_p | Pulse duration |
| T_{stg} | Storage temperature |
| USB | Universal Serial Bus |
| V_{BR} | Breakdown Voltage |
| V_{CL} | Reverse Clamping Voltage |
| V_{ESD} | Electrostatic Discharge Voltage |
| V_{FC} | Forward Clamping Voltage |
| V_R | Reverse Voltage |
| V_{RWM} | Maximum Reverse Working Voltage |

References

- [1] Infineon AG - **Application Note AN210**: Effective ESD Protection Design at System Level Using VF-TLP Characterization Methodology
- [2] Infineon AG - **Application Note AN140**: ESD Protection for Digital High-Speed Interfaces (HDMI, FireWire, ...) using ESD5V3U1U)
- [3] Infineon AG - Recommendations for PCB Assembly of Infineon TSLP and TSSLP Package

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